# CBC2: front-end readout ASIC for the High-Luminosity Upgrade of the CMS Strip Tracker

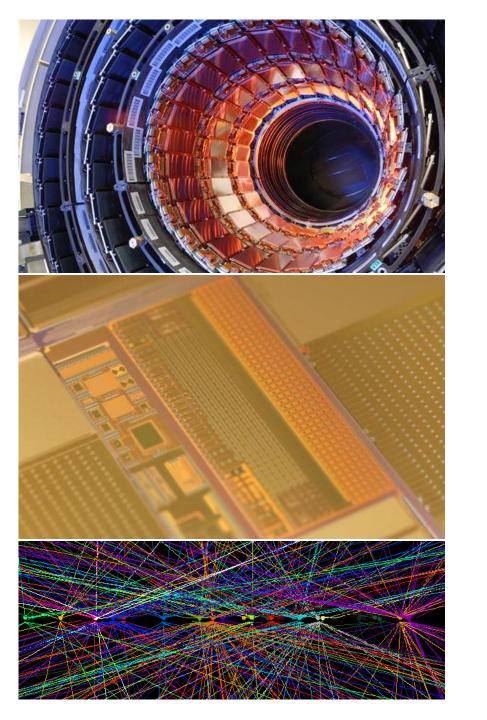
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Imperial College London



Imperial College London





# **Outline**

Tracker upgrade & detector module

•The CMS Binary Chip 2 (CBC2)

CBC2 architecture

•CBC2 performance

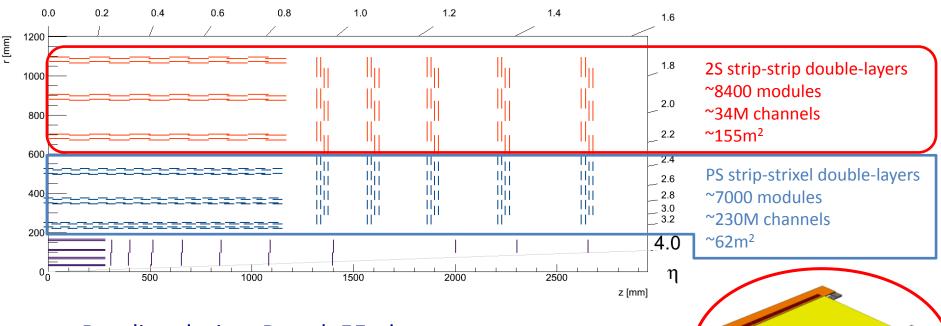
•CBC2 testing

Beam test

•TID test

Summary & Conclusion

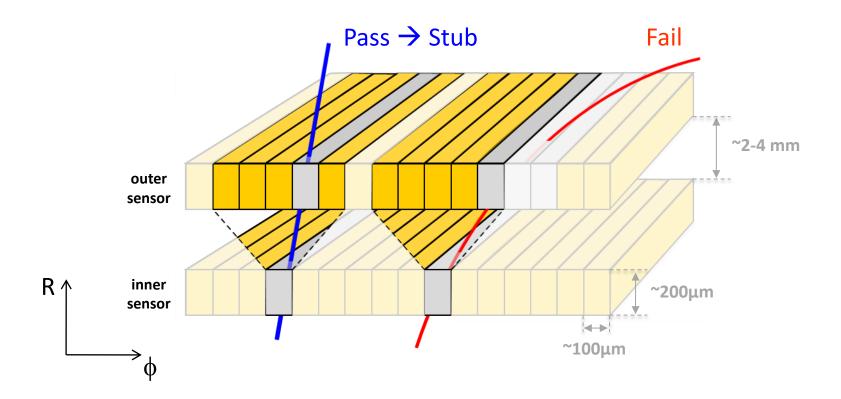
# Phase-II upgrade of the CMS Strip Tracker



- Baseline design: Barrel+5Endcaps
- Based on 2 module types only
- Provides at the same time:
  - readout data upon receipt of L1 trigger
  - trigger data @40MHz



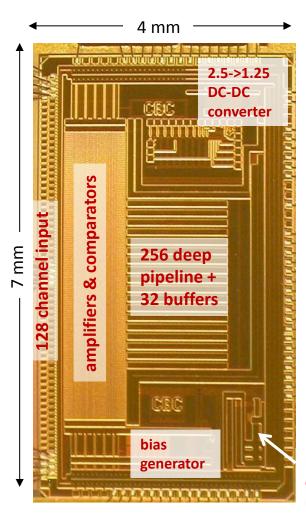
# Basic trigger module concept



- High-PT tracks (stubs) can be identified if cluster centre in top layer lies within a search window in R-Φ (rows)
- $p_T$  cut given by: module radius (z), sensor separation and correlation window

## First version: CBC main features

- IBM 130nm CMOS process
- binary, unsparsified architecture
  - retains chip and system simplicity
  - but no pulse height data
- designed for ~2.5 5cm μstrips < ~ 10 pF</li>
- 128 channels, 50 μm pitch wire-bond
  - either polarity input signal
- not contributing to L1 trigger
- powering test features:
  - 2.5 -> 1.2 DC-DC converter
  - LDO regulator (1.2 -> 1.1) feeds analogue FE
- fast (SLVS) and slow (I2C) control interfaces



Low drop out regulator 11

#### **CBC** → **CBC2**: New Features

- 250µm pitch C4 layout for commercially assembled module back edge wire-bond pads for wafer probe
  - 254 channels for 127 + 127 strips
- correlation logic for stub formation between top & bottom strips vetoes wide clusters
- Front-end circuit improvements
- On-chip test pulse circuit
- Improved DC-DC (CERN)
- received Jan 2013 fully functional

# **CBC2** overview

#### **254 Channels**

- Preamp
- Postamp
- Comparator

#### **Stub-finding logic**

- Cluster width discriminator
- Offset correction
- Coincidence logic
- Inter-chip signals

#### Pipeline memory 256 deep

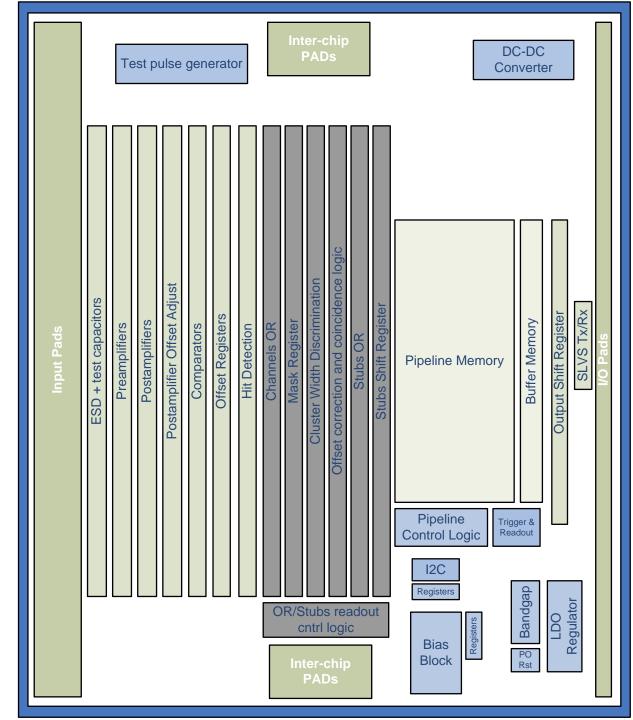
 Dual-port RAM, no SEU immunity

#### **Buffer Memory 32 deep**

 Pipeline address has Hamming encoding

#### **Programmable Biases**

Bandgap LDO Regulator DC-DC Converter I<sup>2</sup>C Interface SLVS I/O

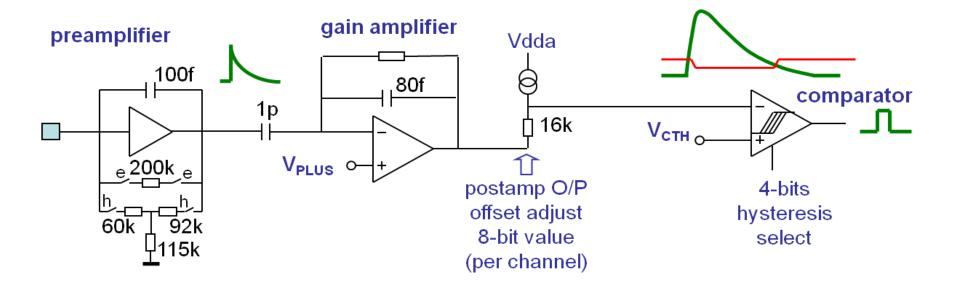


# **Front End: Design**

# **CBC2 Front End Specifications**

Detector Type:	Silicon Strip
Signal Polarity:	both (electrons and holes)
Strip length:	2.5 – 5cm
Strip Capacitance:	< 10pF
Coupling:	AC or DC
Detector leakage:	up to 1uA leakage current compensation
Noise:	<1000e RMS for 5pF sensor capacitance
Overload recovery:	normal response within ~ 2.5μs after 4pC signal
Power:	~500µW / channel (for 5pF strips)
Power supply:	1.1 V (front end supplied through LDO to get supply noise rejection)
Gain	50mV/fC
Dynamic range:	Linear up to 4fC
Timewalk:	<16ns for 1.25fC and 10fC signals with comp. thresh. set at 1fC

#### Front end



#### **PreAmplifier:**

- 100fF feedback capacitor
- Selectable resistive feedback network for leakage current of both polarities
- 20ns time constant

#### **Gain Amplifier:**

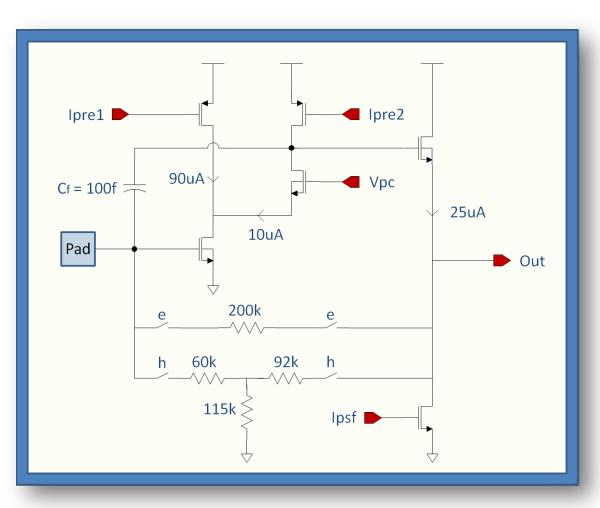
- Designed for both e<sup>-</sup> and h<sup>+</sup>
- Coupling capacitor removes leakage current shift
- Offset programmable independently for every channel (8b)

#### **Comparator:**

- Global threshold (8b)
- Internal programmable hysteresis

# **Charge Sensitive Preamplifier**

- Single ended cascode + source follower
  - nMOS input to reduce power supply noise
  - 1/f corner quite low

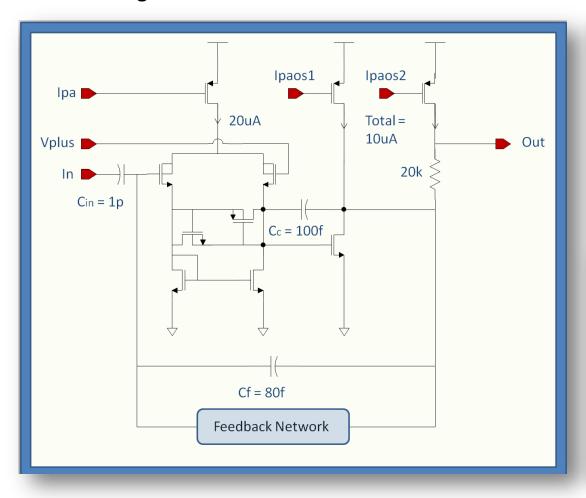


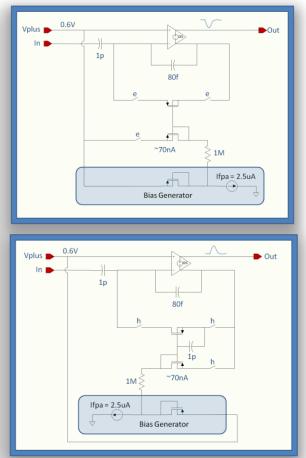
- Cascode and input devices optimized independently
- Selectable resistive feedback for e<sup>-</sup> and h<sup>+</sup>
  - T-network in holes mode to increase headroom with leakage shift
- 20ns peaking time

# **Gain Amplifier**

- 2stage differential, inverting
- AC-coupled to preamp
- x 12.5 gain

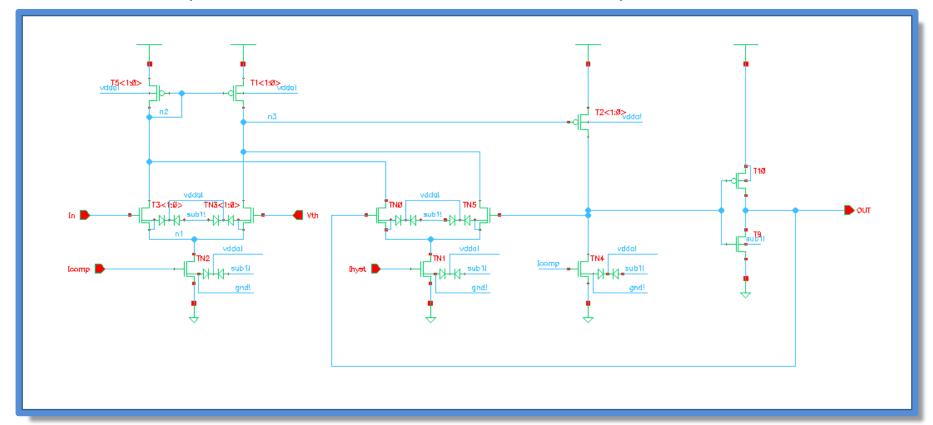
- Diode-connected transistors improve recovery time for very large (HIP) signals
- Selectable e<sup>-</sup> and h<sup>+</sup> feedback network
- 8b selectable currents

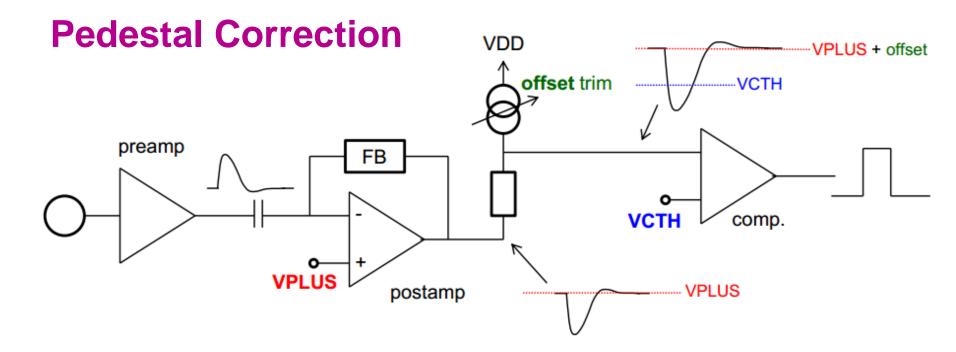




# **Comparator**

- 2-stage differential
- Internal programmable hysteresis (4b global)
- Transition from analog/digital domains
- Timewalk within specs
- Comparator and gain amplifier pedestals corrected in one step with programmable DC-shift of comparator input
- 2 modes of operation: normal return to baseline or 25ns-pulsed





3 voltage levels to program:

VPLUS sets DC point at output of postamp
Offset current adds an extra positive DC shift
VCTH is the comparator threshold

VPLUS, VCTH are global (same value for all channels)
Offset current is individually adjustable for every channel

#### **Tuning procedure:**

- 1. Set all **offsets** to a value not too small (to avoid slew-rate limiting at comparator input node
- 2. Set **VCTH** in middle region of input range
- Sweep VPLUS to find value corresponding to average channel s-curve midpoint (1/2 channels firing) → This is the final value for VPLUS
- Tune channel offsets to achieve midpoint on
   VCTH → tune pedestal (not using test pulse)
   for few channels at once

# **Front End: Test Results**

#### **Gain measurements**

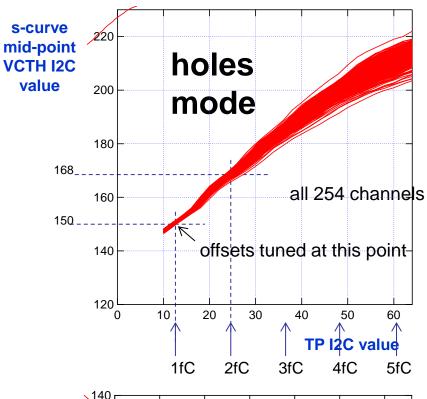
sweep global comparator threshold VCTH to get s-curves for range of test pulse amplitudes

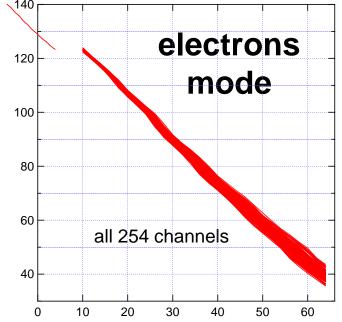
plot s-curve mid-points vs. TP amp

rough calculation in 1÷2fC region (assumes TP value of 12 / fC)

$$(168 - 150) \times 2.5 \text{ mV}^* = 45 \text{ mV/fC}$$

(\* from VCTH bias sweep measurements)



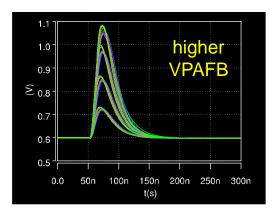


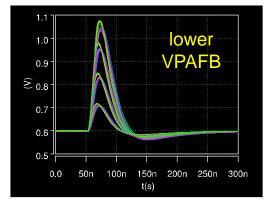
# Gain Amplifier feedback resistor control

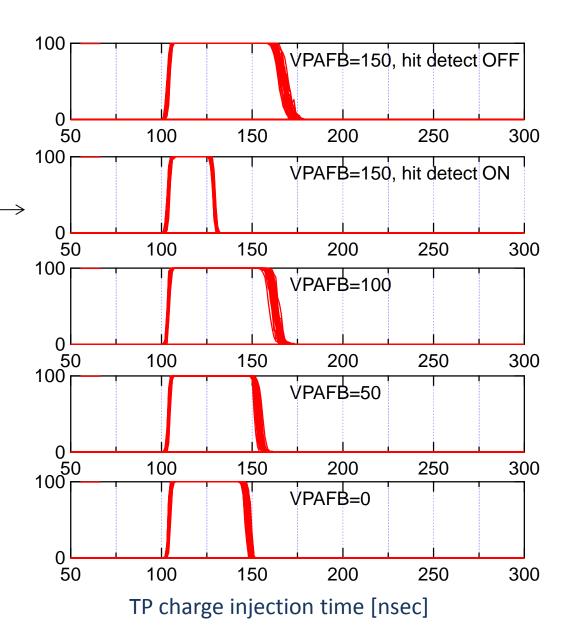
can see effect of VPAFB using test pulse sweep - smaller values give shorter pulse length

hit detect circuit works - only single hit in pipeline irrespective of how long comp O/P stays high

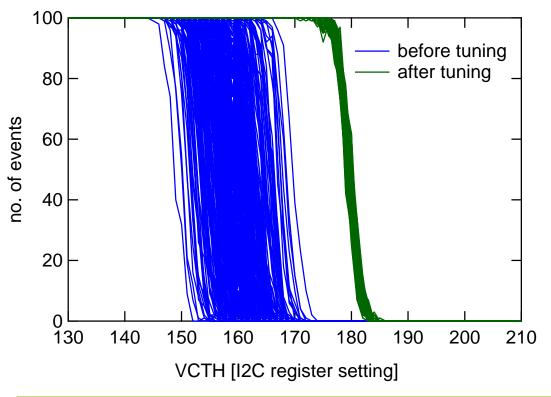
> ~ 2 fC signal \_\_\_\_\_ 1 fC comp. thresh





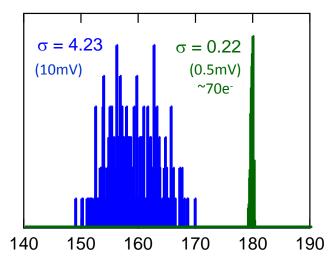


# S-curves and tuning

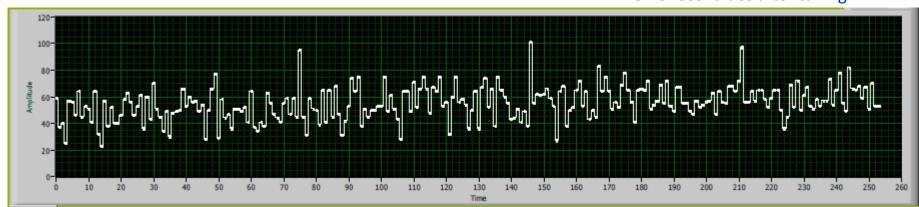


# 254 S-curves measured with on-chip test pulse

#### S-curve mid-points tuned to ~mV level



254 offset values after tuning



# **Stub Finding Logic**

# Stub finding logic

#### Cluster width discrimination (CWD) logic

exclude clusters with hits in >3 neighbouring channels wide clusters not consistent with high pT track

#### Offset correction & correlation logic

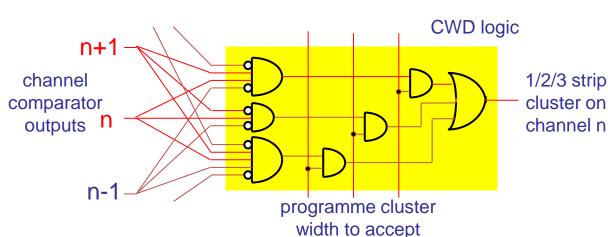
for a cluster in bottom layer, look for correlating cluster occurring in window in top layer

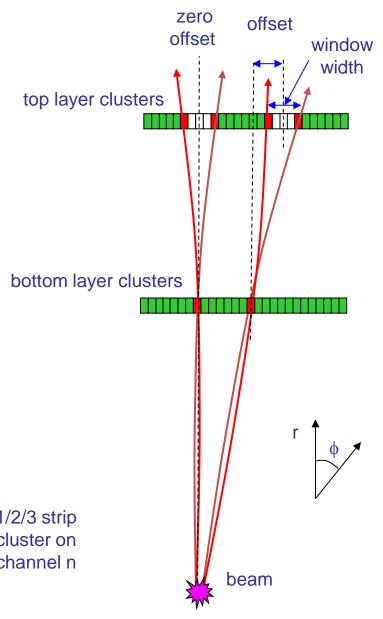
#### window width controls pT cut

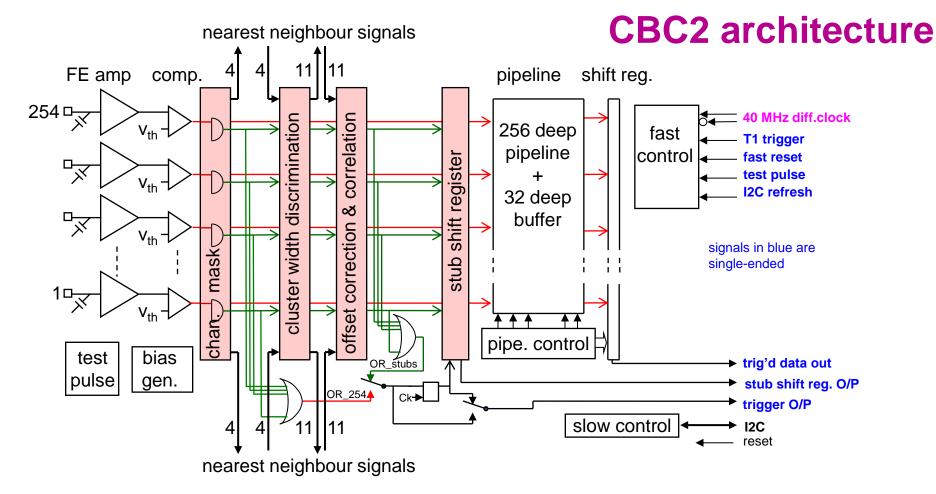
- stub found if cluster in bottom layer corresponds to cluster within window in top layer
- programmable up to  $\pm$  8 channels

offset defines lateral displacement of window across chip

programmable up to ± 3 channels







**254 channels:** 127 from each sensor layer

test pulse: charge injection to all channels (8 groups of ~32)

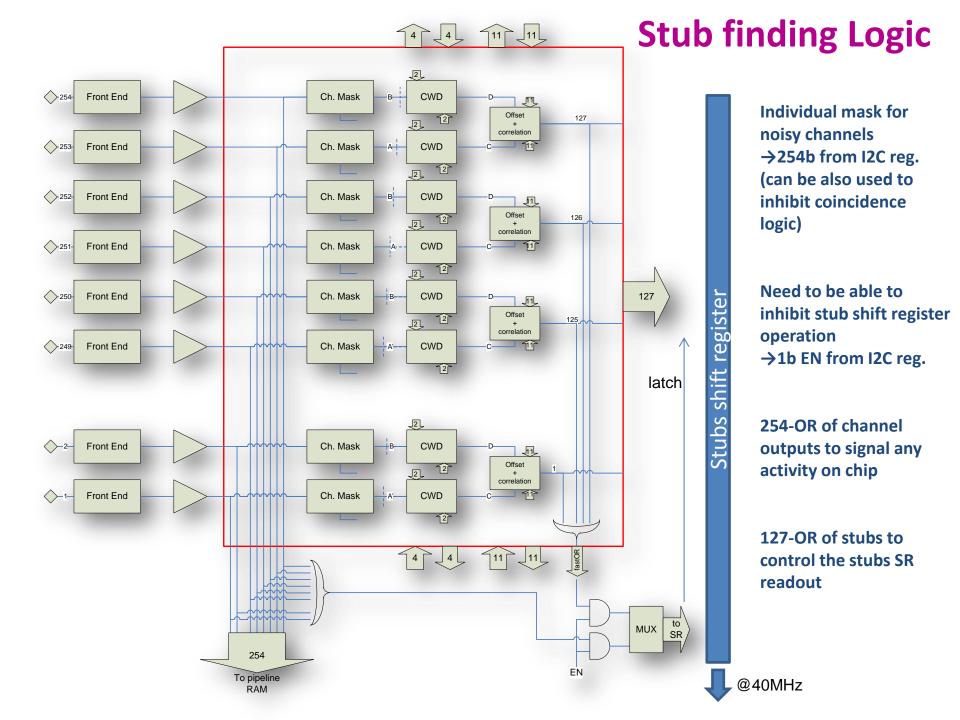
**channel mask:** block noisy channels from trigger logic **Cluster Width Discriminator logic:** exclude wide clusters >3

Offset Correction and Correlation logic: correct for phi offset across module and correlate between layers

trigger output: 1 bit per BX indicates stubs have been found

**stub shift register:** test feature - shift out result of correlation operation at 40 MHz

triggered data out: unsparsified binary data frame in response to L1 trigger



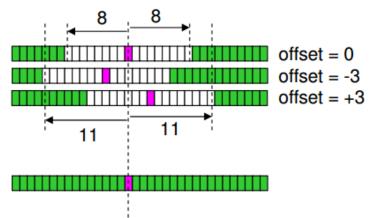
# neighbour chip signals - CWD O/Ps

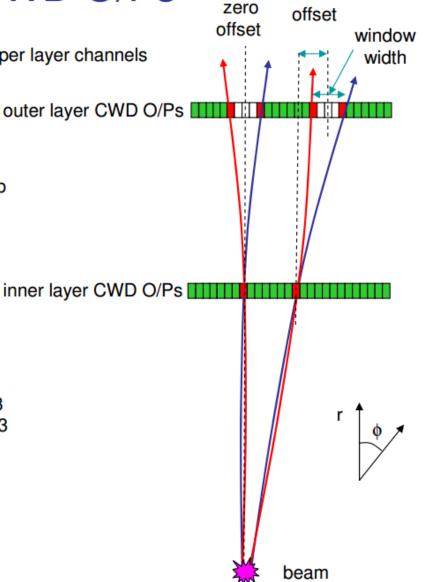
need programmability of **offset** and **window** width for upper layer channels to correlate with hit in inner layer

window defines Pt cut width programmable up to +/- 8 channels

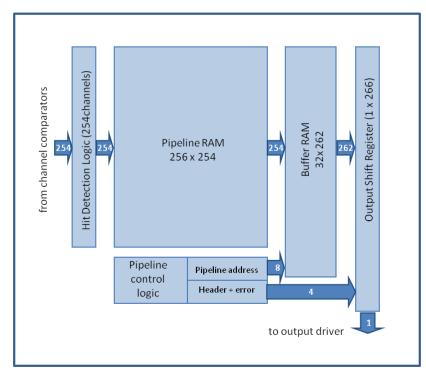
offset defines lateral displacement of window across chip programmable up to +/- 3 channels

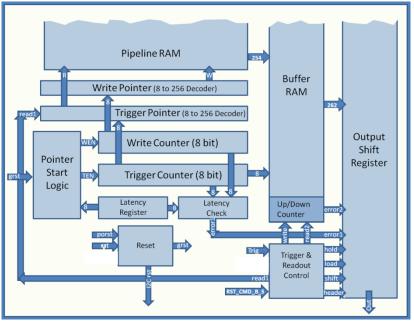
- => 11 signals to transmit to neighbouring chip 11 to receive from neighbouring chip
  - = 22 signals





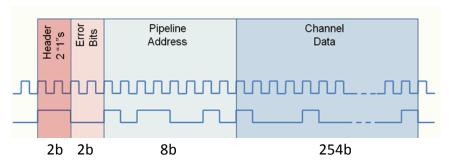
# **Digital Back End: Design**





#### Data buffer and readout

- 256-deep memory → max 6.4µs L1 trigger latency
- Dual-port SRAM (SEU tolerable for data)
- 32-deep additional buffer for events awaiting readout
- Data serialized in 266 long packets

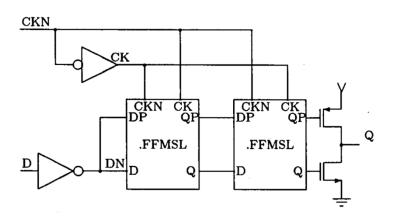


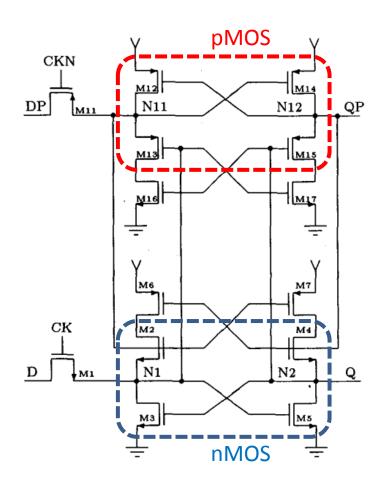
- Write and Read pointers separated by programmable latency
- 2 error bits:
  - Monitor the difference between Wr/Rd pointers against programmed latency
  - Buffer overflow
  - The address of the trigger counter is also a useful way to check the synchronization of different chips on the module

# Liu-Whitaker SEU-hardened Flip-Flop

#### 3 fundamental concepts:

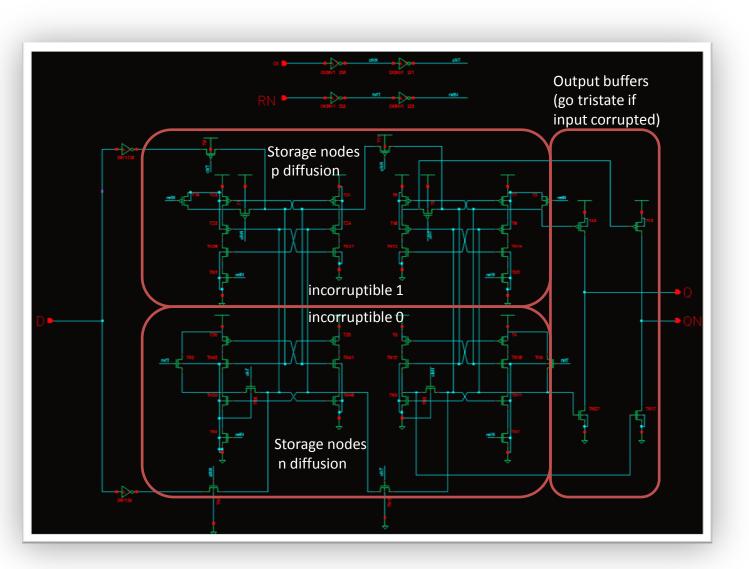
- Redundancy
- 2. Restoring feedback
- Induced current flows from n-diffusion to p-diffusion → if all pMOS transistors: inherently-hard 1; if all nMOS: hard 0





Liu, M. Norley, and Sterling Whitaker. "Low power SEU immune CMOS memory circuits." *Nuclear Science, IEEE Transactions on* 39.6 (1992): 1679-1684.

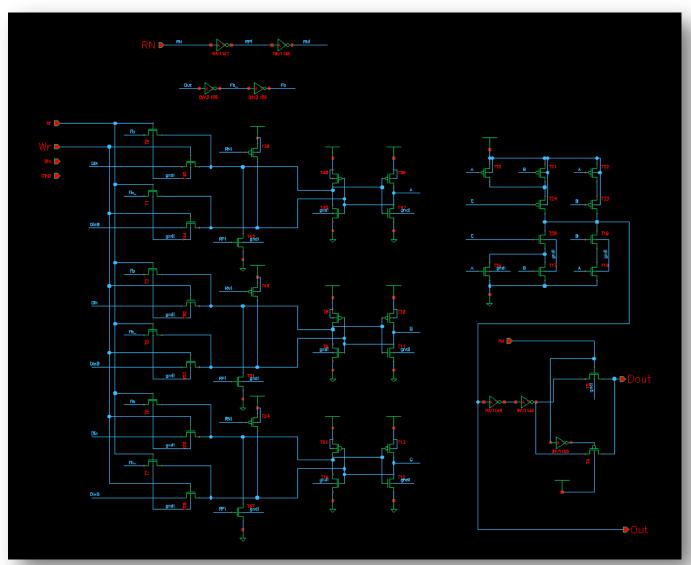
# Liu-Whitaker SEU-hardened Flip-Flop (2)



Used in:

- •pipeline control circuit
- •Data/stub shift registers

# SEU-tolerant I<sup>2</sup>C register

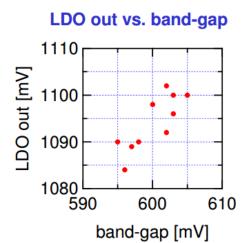


- > 300 8b I2C registers
   2page system
  - Chip modes
  - Bias settings
  - Comparator thresholds
  - Channel masks
  - **–** ..
- Triple RAM Cells with voting circuit
- Settable and resettable versions
- Can be "refreshed" by external signal to avoid cumulative errors

#### **Power elements**

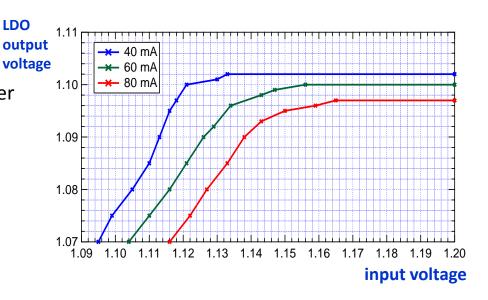
#### Low-dropout linear regulator

- provides clean, regulated rail to analog FE (uses CERN bandgap) ~ 1.2 Vin, 1.1 Vout
- load currents 40, 60, 80 mA
- dropouts ~ 30, 55, 70 mV (approx.)
   DC shift due to series resistance (measured on wire-bonded chip)



#### DC-DC: (CERN)

- CERN on-chip switched capacitor converter
- 2.5V → ~1.2V Can be used to power the
   CBC2
- Improved version wrt CBC1



## **Noise & Power**

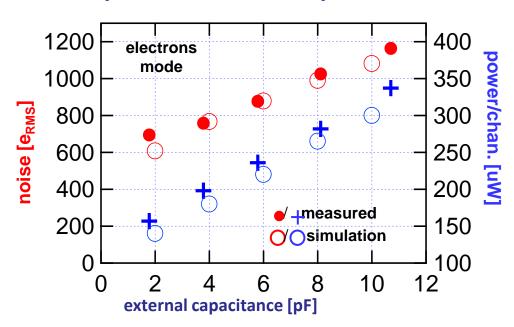
#### **Analog**: $130 + (21 \times C_{in}[pF]) \mu W$

**Digital**:  $50\mu$ W **Trig. logic:**  $<50\mu$ W

**Total**:  $<230 + (21 \times C_{in} [pF]) \mu W$ 

APV25 ~2.6mW (long strips)

#### noise & power vs. external capacitance



- Noise and power depends on external input capacitance
- The current settings in the front-end are adjusted to maintain the same pulse shape for different C<sub>in</sub>
- Results almost identical for e<sup>-</sup> and h<sup>+</sup>
- $\rightarrow$  specification of 1000e<sub>RMS</sub> for 5cm strips met with 350 $\mu$ W/channel

# Layout

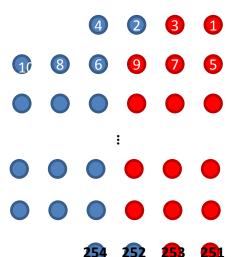
# **C4 BumpBond Pads**

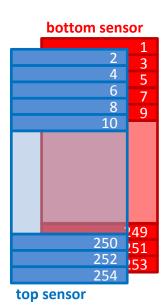
# 250um 250um

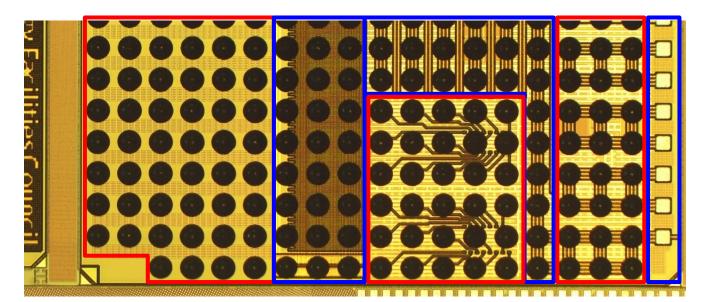
Input pads arranged in rows of 6 because of constraint in the routing of tracks on the hybrid

#### **Hybrid footprint:**

Inputs from top sensor Inputs from bottom sensor

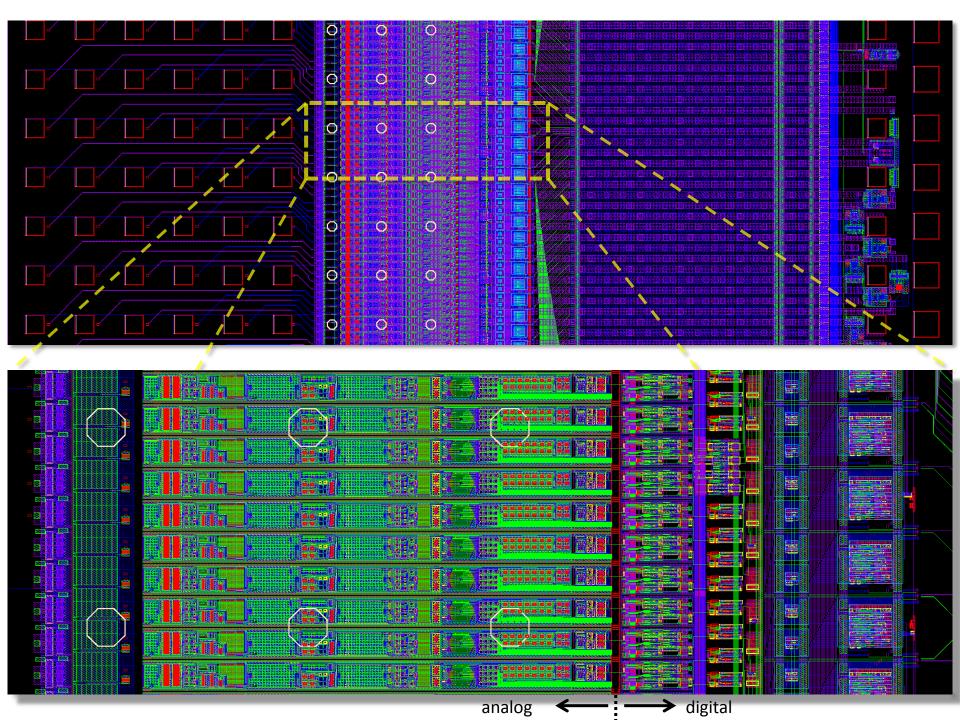




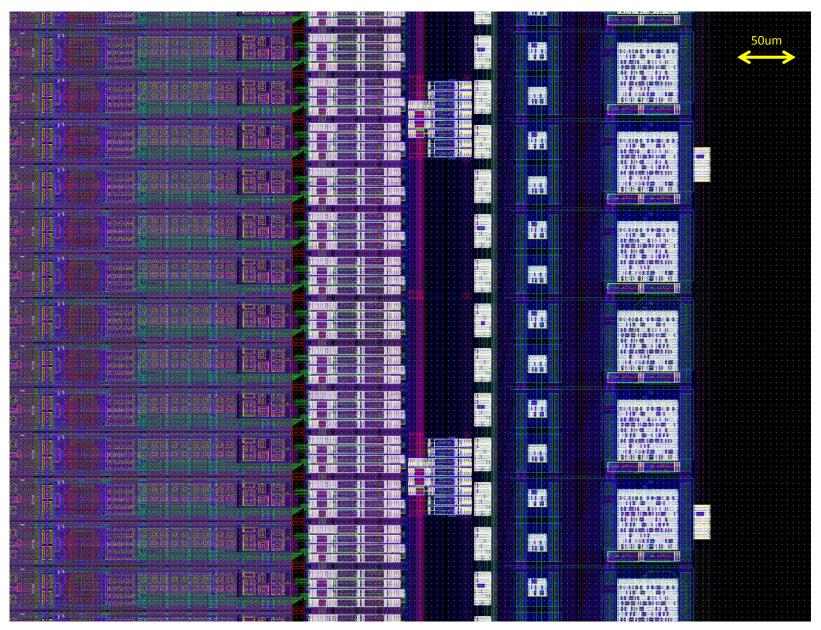


#### 809 pads:

- Input pads
- Dummy pads
- Inter-chip pads
- Gnd pads
- I/O pads
- Wire-bonded pads
  BB WB split run



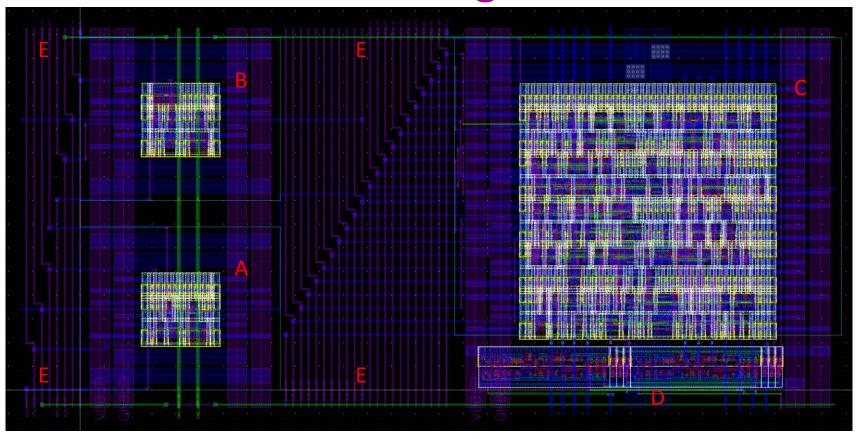
# **Digital part - Detail**



# **Digital part - Detail**

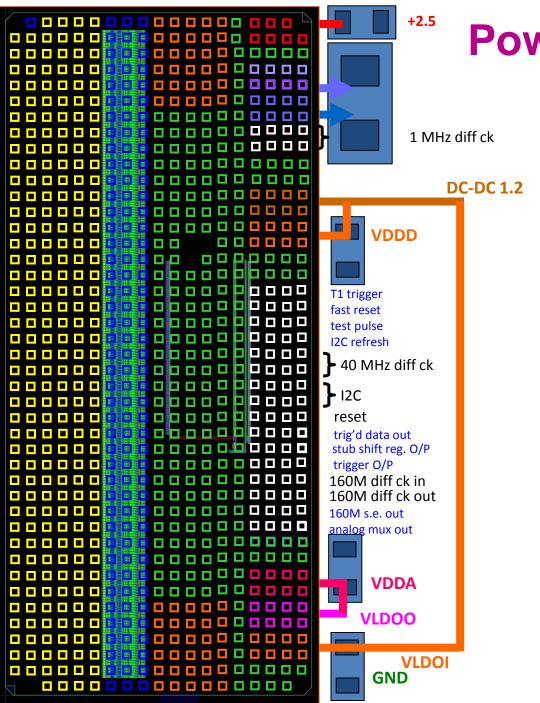


# **Coincidence logic - Detail**



- A: Cluster width discrimination for bottom sensor hits
- B: Cluster width discrimination for top sensor hits
- C: Coincidence logic (with programmable window and offset correction)
- D: Shift register for stubs readout and shadow SR for readout control
- E: lines to/from previous/next channels (propagate for ~1mm (11\*80um))

Inputs
dummy
prev/next
chip
gnd



### Power distribution

NB: the last column of PADs to the right are wire-bondable, they will not be routed on hybrid (->possible to reach the 3 pads to their left)

All but 160MHz output pads have redundancy

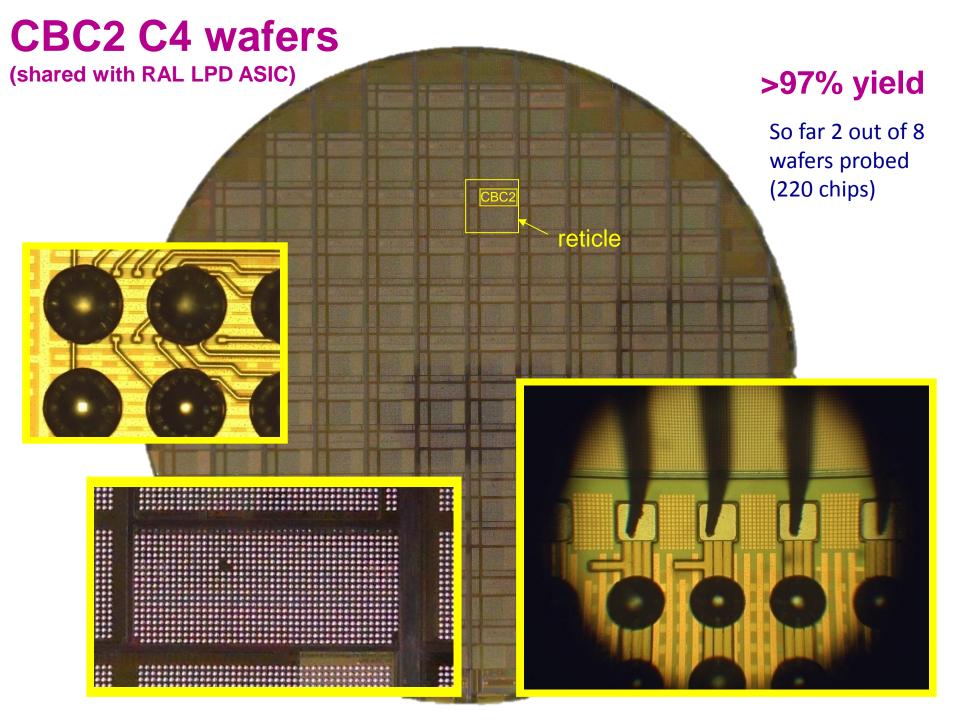
lines and arrows show direction of power flow (GND not shown)

#### note:

DC-DC 1.2 not connected to VDDD or VLDOI on-chip

LDO output also connected to VDDA offchip

(the idea is to maximise possible effectiveness of off-chip filtering)



# **CBC2** Testing Activities

### **CBC2** testing activities

### Wire-bond CBC2

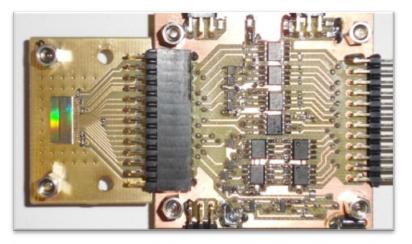
- Useful to develop wafer probe procedures
- X-rays TID testing

### 2xCBC2 hybrid

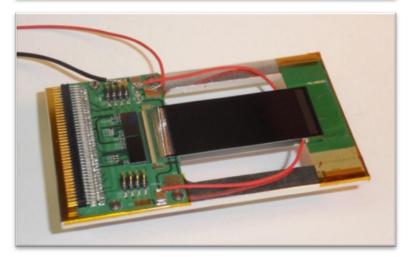
- Hybrid characterization and chip integration
- Bump-bonded ASICs
- Inter-chip links & logic

### 2xCBC2 mini-module + sensor

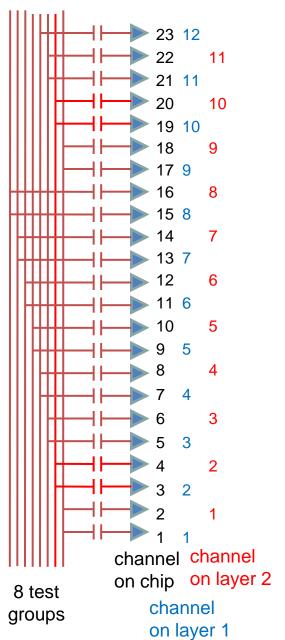
- Sr-90 source
- Cosmic rays
- Beam Test

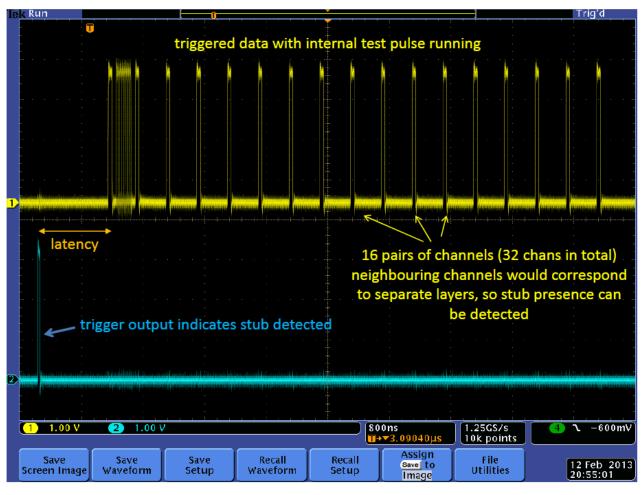






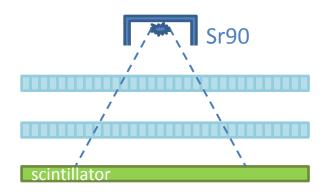
### Results with test pulse

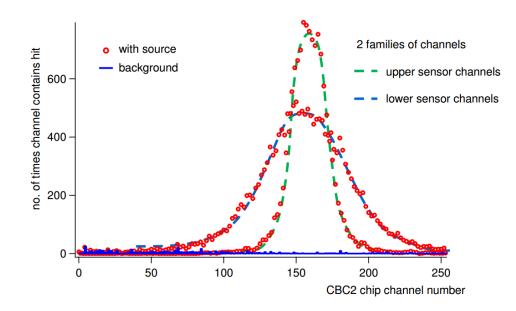


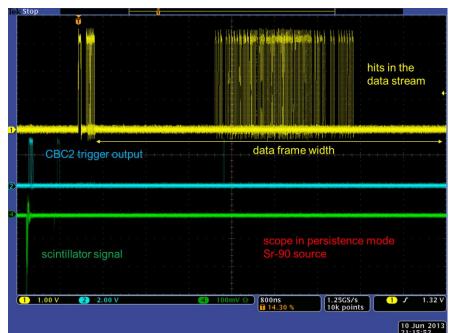


→ Test pulse together with individually-programmable channel masks can be used to fully exercise the coincidence logic

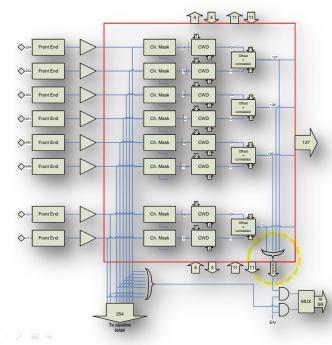
# Logic tests using beta source

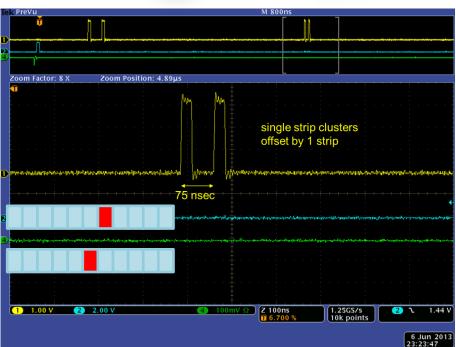


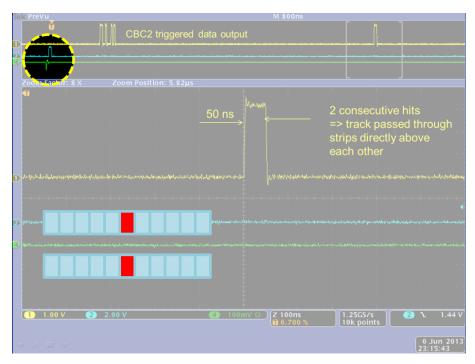


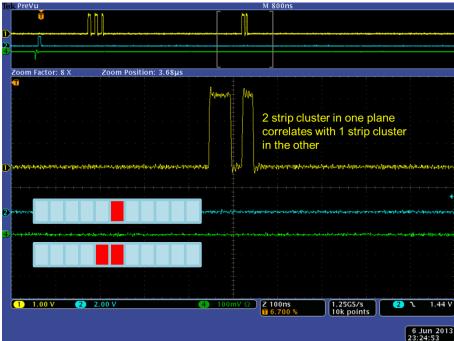






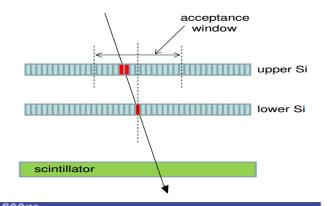


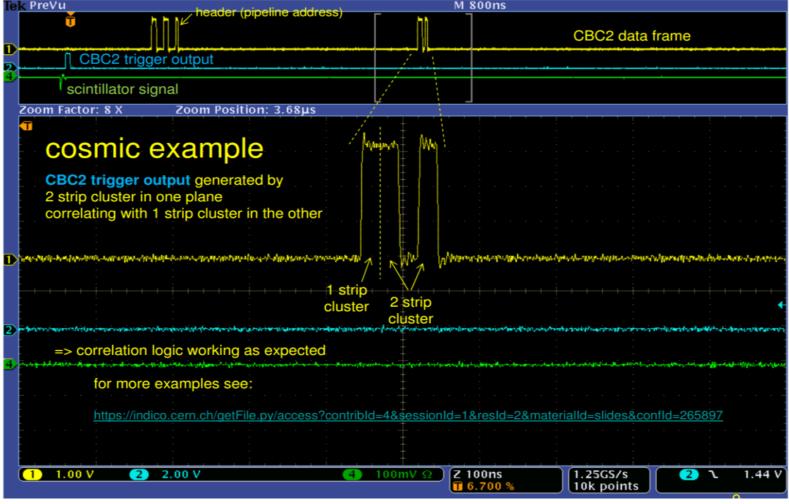




### Logic tests using cosmics

NB: very low rate (<<1Hz) even with maximum coincidence window in upper sensor

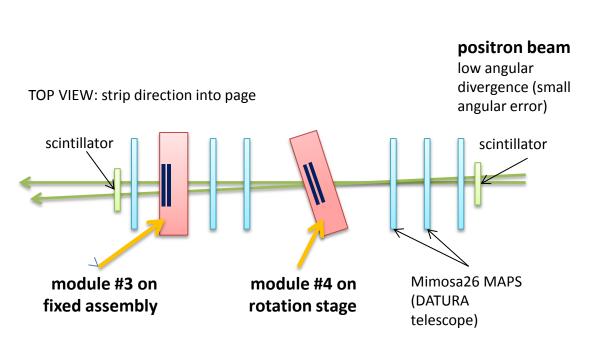




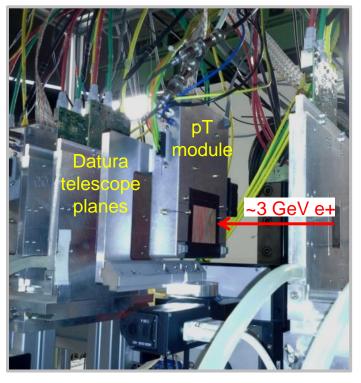
# **Beam Test**

### Pt module beam test at DESY

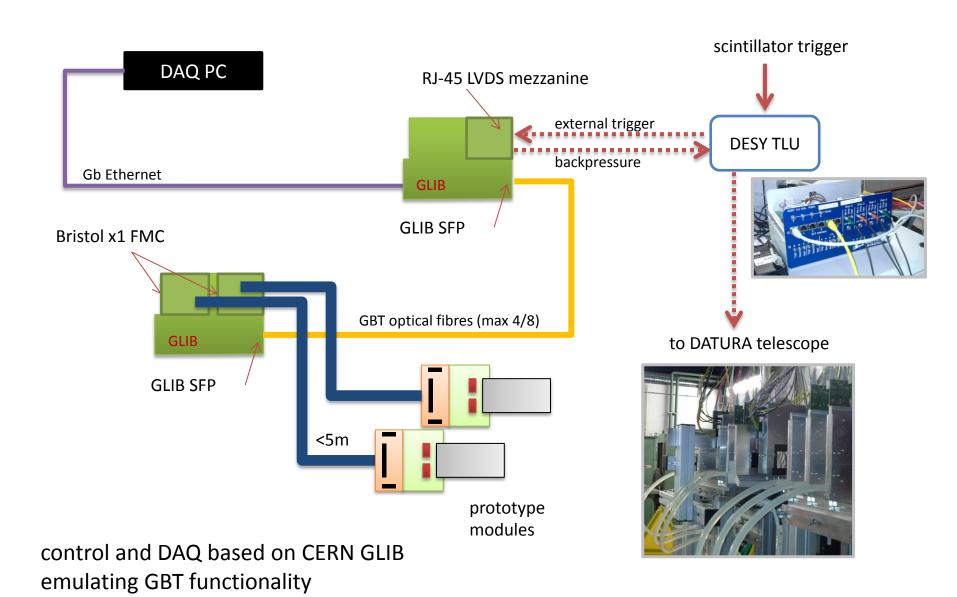
- December 2013
- 4 GeV positron beam
- Datura telescope + 2 pT modules (1 rotatable to simulate B-field effect) + 2 different strip sensors
- Custom control and DAQ







### **Beam test DAQ**

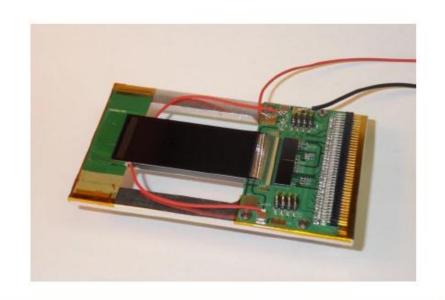


### Pt modules & sensor variants

### modules taken to DESY

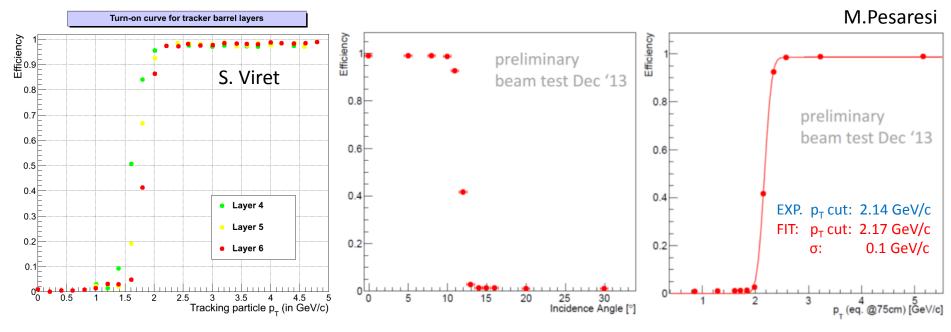
three pt modules taken to DESY

- two different sensor types
- one module left as backup



module #	sensor	sensor type	pitch [um]	thickness [um]	length [mm]	# strips	comments	tested
3	Infineon	n-type	80	300	50	256	region of disconnected channels	yes
4	CNM	p-type	90	270	54	254		yes
1	Infineon	n-type	80	300	50	256	noisy strips, disconnected channels, odd low bias behaviour	no/ backup

### Beam test results



Pt Selection cut: simulation



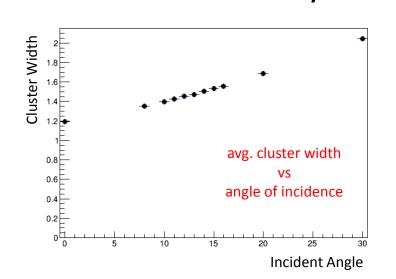
measured efficiency



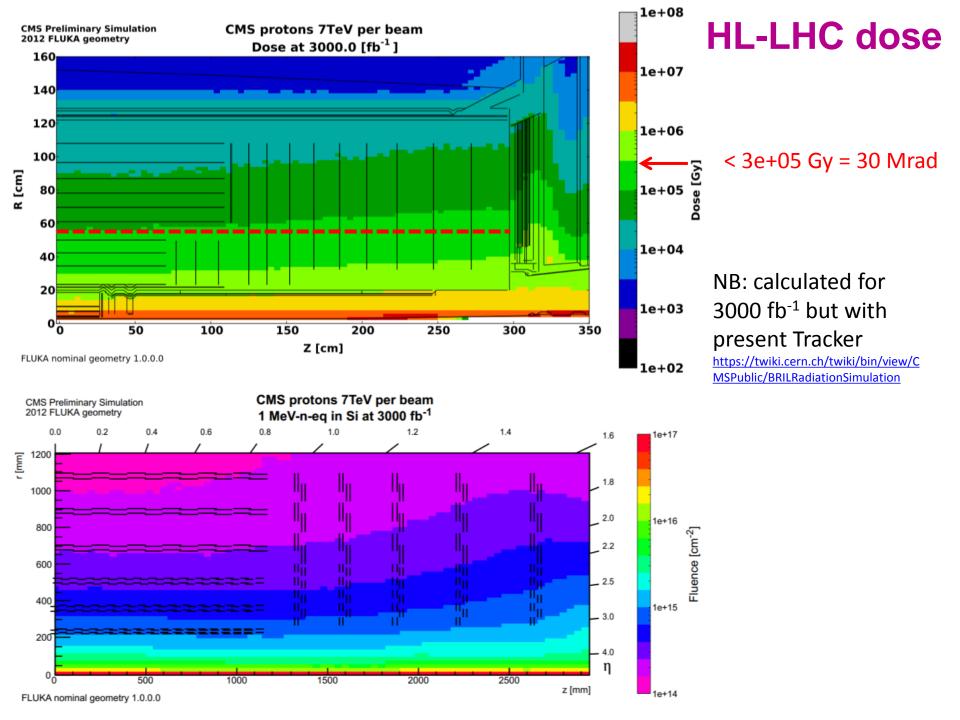
reconstructed p<sub>T</sub> cut of r=75cm layer

### Other measurements include:

- Study of cluster width
- System noise
- Beam profile

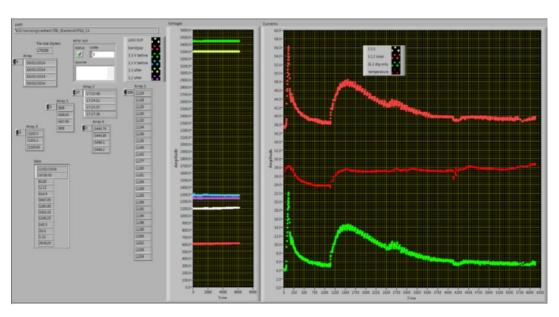


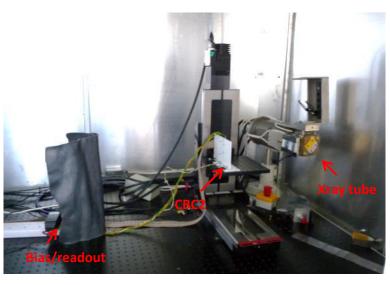
# **Total Ionizing Dose Testing**



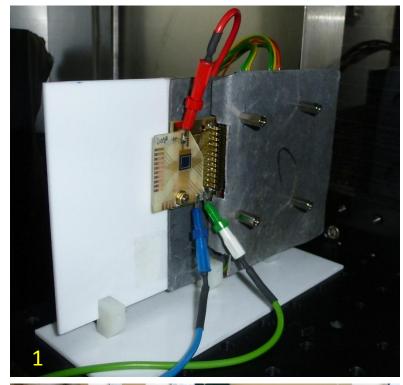
### **Total Ionizing Dose test**

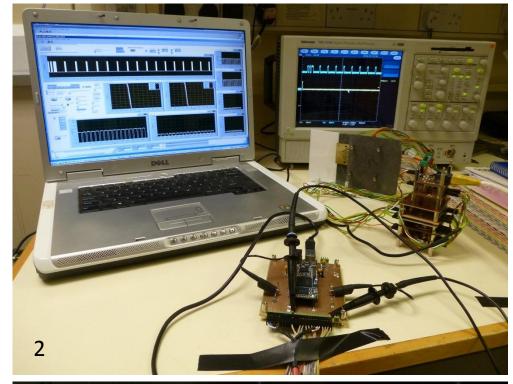
- First xray irradiation to 10 Mrads
- CBC2 operated continuously during irradiation
- monitored currents, biases, pedestal, noise
- no significant change in performance, moderate increase in current before annealing
- Next: TID test up to ~50 Mrads

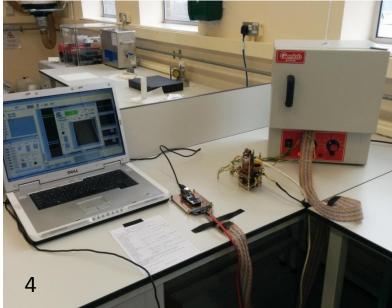




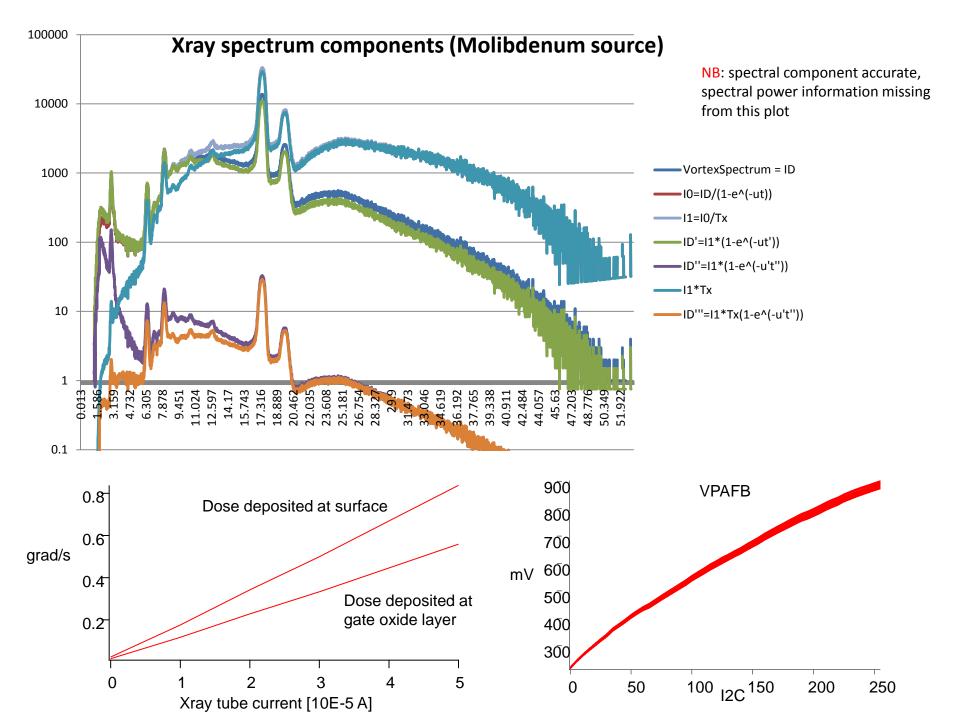












# **Conclusions and Future Work**

### **CBC3:** the final prototype

#### **Sensor choice:**

n-on-p, AC coupled, strip length up to 8 cm (~12 pF) => polarity defined, no DC sink/source requirement

#### Front end amplifier:

- adjust for 1V VDDA
- re-examine pulse shape for dead-time issue want pulse that returns to baseline within 50 ns some overshoot unavoidable
- adjust preamplifier for larger sensor capacitance

To maintain current noise performance for 8cm strips:

noise 
$$\propto \frac{c}{\sqrt{I_{DS}}}$$
,  $g_m \propto I_{DS}$ 

→ to compensate (8/5) x C need 2.6x current in input device!

#### **Comparator:**

- Possibility to include 2 comparators/channel:
   5σ and 3σ thresholds
- (1 chan >  $5\sigma$ ) OR (2 neighbours >  $3\sigma$ )=> hit
  - → more signals to cross chip boundaries
  - →extra ~50uW/channel
- Additional circuit to suppress HIPs (block comp. out if longer than several BXs)

#### **Trigger Rate & Latency:**

- Pipeline length increase to 12 25μsec
- L1 Trigger rate increase: 500kHz 1MHz

#### **Channel masking:**

Sparsification (in concentrator) becomes mandatory for 1 MHz trigger rate

#### **Stub definition:**

- ½ strip cluster resolution → 8b address
- 5b bend information
- priority selection of 3 highest-pT stubs
- Offset correction: 4 domains/chip (2 in CBC2)

#### Stub readout:

- 13b/stub, up to 3 stubs/BX
- 6 SLVS differential pairs @ 320Mbps

#### **Changes to pad layout:**

Considering relaxing the requirements for hybrid manufacturers by increasing the pitch of bump-bond pads

# **Summary & Conclusions**

### Two successful full-size prototypes of new Outer

#### **Tracker ASIC**

- ✓ CBC2 working to specs
- ✓ Some front-end improvements over CBC1
- ✓ Stub finding logic functioning
- ✓ Power features (LDO & DC-DC) operational

### First prototype version of 2S module in hand

- ✓ First demonstration of bump-bonded ASIC for strip readout
- ✓ Ready to be distributed to collaborating institutes
- ✓ First beam test followed by ionizing radiation test and future SEU studies

